

## N-Channel Enhancement Mode Power MOSFET

### MAIN CHARACTERISTICS

$I_D$	13A
$V_{DSS}$	500V
$R_{DSON-typ}$ (@ $V_{GS}=10V$ )	0.36 $\Omega$

### FEATURES

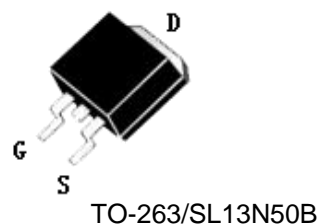
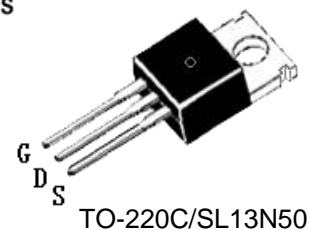
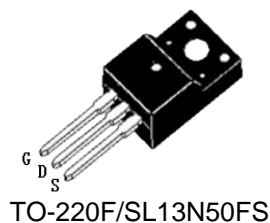
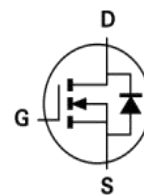
- Fast Switching
- Low ON Resistance
- Low Gate Charge
- 100% Single Pulse avalanche energy Test

### APPLICATIONS

- Power switch circuit of adaptor and charger.

### MECHANICAL DATA

- Case: Molded plastic
- Mounting Position: Any
- Molded Plastic: UL Flammability Classification Rating 94V-0
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Solder bath temperature 275 $^{\circ}C$  maximum, 10s per JESD 22-B106



## Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbol	Value		Unit
		220F	220C/263	
Drain-Source Voltage	$V_{DS}$	500		V
Gate-Source Voltage	$V_{GS}$	±30		V
Continue Drain Current	$I_D$	13		A
Pulsed Drain Current (Note1)	$I_{DM}$	52		A
Power Dissipation	$P_D$	60	150	W
Single Pulse Avalanche Energy (Note1)	$E_{AS}$	840		mJ
Operating Temperature Range	$T_J$	150		°C
Storage Temperature Range	$T_{STG}$	-55 to +150		°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.08	0.83	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	100	62.5	°C/W

Note1:Pulse test: 300  $\mu$ s pulse width, 2 % duty cycle

## Electrical Characteristics at Tc=25°C unless otherwise specified

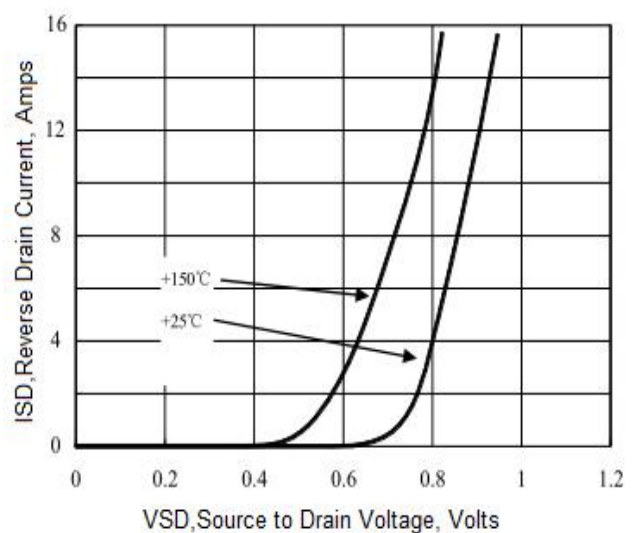
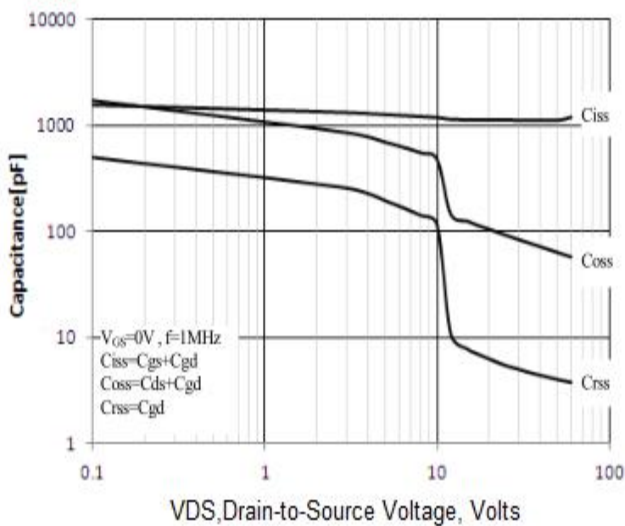
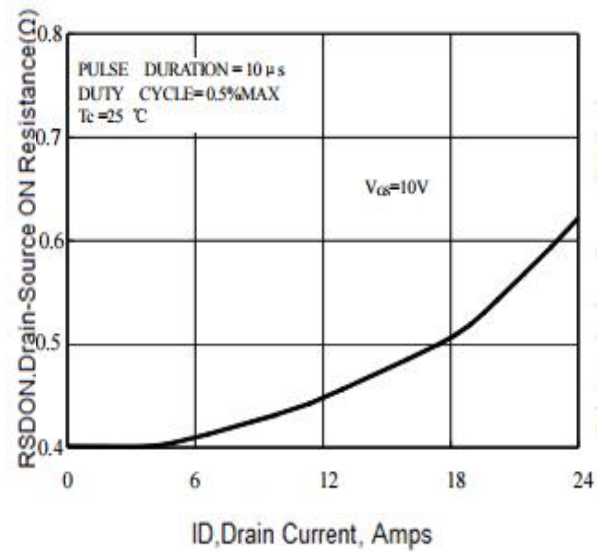
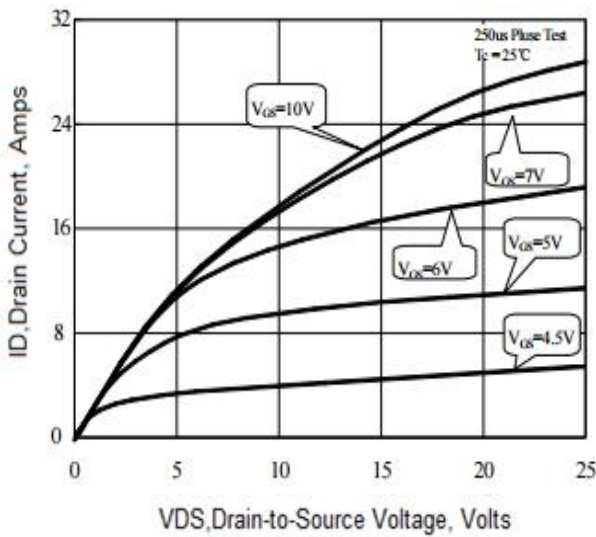
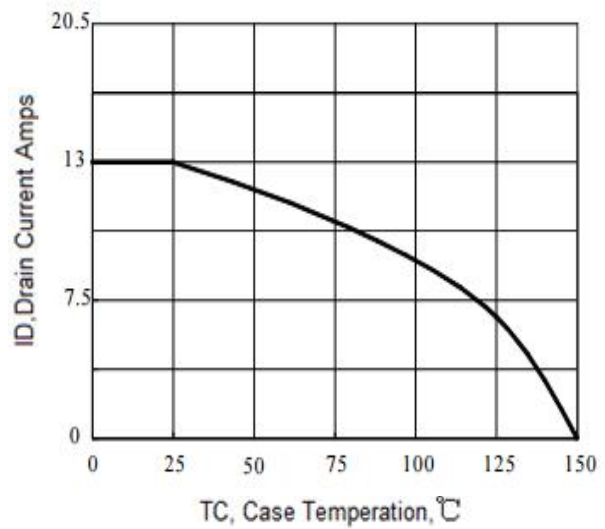
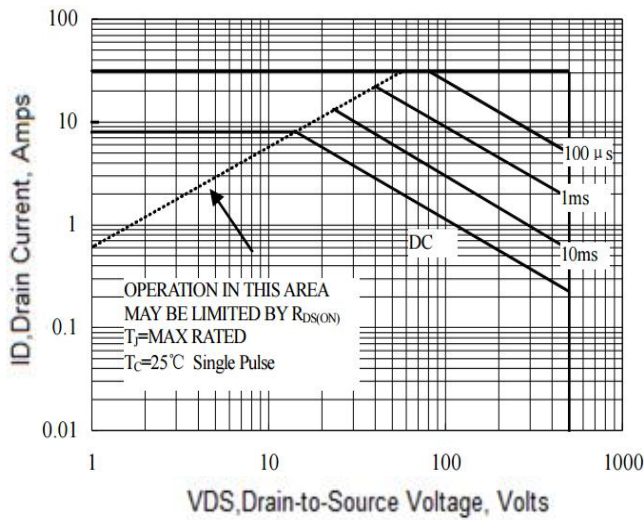
Characteristics	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_D = 250 \mu A$	$BV_{DSS}$	500	-	-	V
Drain-Source Leakage Current	$V_{DS} = 500 V, V_{GS} = 0 V$	$I_{DSS}$	-	-	1	$\mu A$
Gate Leakage Current	$V_{GS} = \pm 30 V, V_{DS} = 0 V$	$I_{GSS}$	-	-	±100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	$V_{GS(th)}$	2	-	4	V
Drain-Source On-State Resistance	$V_{GS} = 10 V, I_D = 6.5 A$	$R_{DS(on)}$	-	0.36	0.5	$\Omega$
Forward Transconductance	$V_{DS} = 15 V, I_D = 6.5 A$	gfs	-	13	-	S
Input Capacitance	$V_{GS} = 0 V, V_{DS} = 25 V,$ $f = 1 MHz$	$C_{iss}$	-	1560	-	pF
Output Capacitance		$C_{oss}$	-	160	-	pF
Reverse Transfer Capacitance		$C_{rss}$	-	17	-	pF
Turn-on Delay Time(Note2)	$I_D = 13 A, V_{DD} = 250 V,$ $R_G = 10 \Omega$	$t_{d(ON)}$	-	13	-	ns
Rise Time(Note2)		$t_r$	-	16	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	40	-	ns
Fall Time(Note2)		$t_f$	-	17	-	ns
Total Gate Charge(Note2)	$I_D = 13 A, V_{DD} = 400 V,$ $V_{GS} = 10 V$	$Q_G$	-	40	-	nC
Gate to Source Charge(Note2)		$Q_{GS}$	-	8	-	nC
Gate to Drain Charge(Note2)		$Q_{GD}$	-	16	-	nC

## Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Characteristics	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current		$I_S$	-	-	13	A
Maximun Body-Diode Pulsed Current(Note2)		$I_{SM}$	-	-	52	A
Drain-Source Diode Forward Voltage	$I_{SD} = 13 A$	$V_{SD}$	-	-	1.4	V
Reverse Recovery Time(Note2)	$I_{SD} = 13 A, V_{GS} = 0 V,$ $di_F / dt = 100 A/\mu s$	trr	-	482	-	ns
Reverse Recovery Charge(Note2)		Qrr	-	1.7	-	$\mu C$

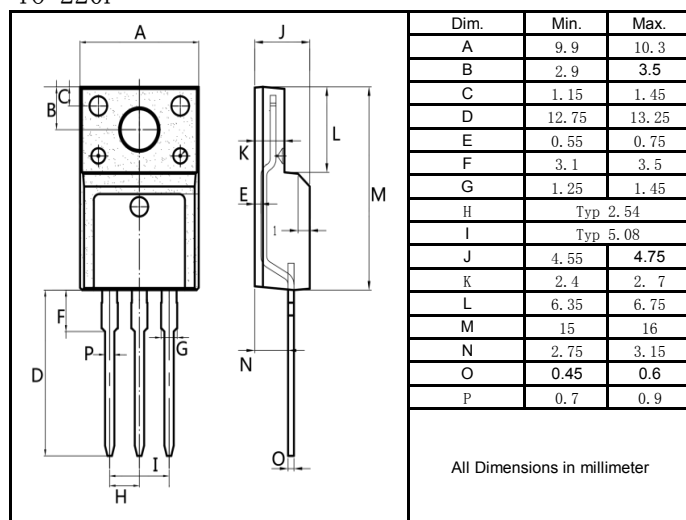
Note2:Pulse test: 300  $\mu$ s pulse width, 2 % duty cycle

## RATINGS AND CHARACTERISTIC CURVES

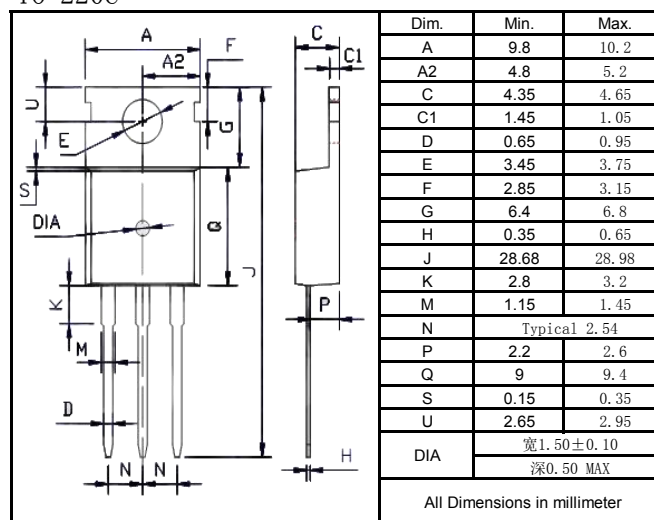


## Package Outline Dimensions millimeters

### T0-220F



### T0-220C



### T0-263

